A nisotropic transport in the overdoped H igh-T c superconductors within the V an H ove scenario

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Recent R am an experim ents[1] done in B i_2 S r_2 C a C u_2 O₄ have found that antinodal quasiparticles become insulating when the doping is varied from overdoped to optim ally doped while nodal quasiparticles rem ain m etallic. W e propose a simple explanation based on the incoherence of the spectral function in the antinodal direction due to the strong scattering su ered by the quasiparticles in the proximity of the Van H ove singularity.

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Recent Raman experiments[1] have found a strong anisotropy of the electron relaxation in B $i_2 S r_2 C a C u_2 O_4$ when the doping varies from the optimal region to the overdoped region. W hile the nodal quasiparticles remain m etallic and hardly vary with temperature and doping the antinodal quasiparticles su eram etal-insulator transition at p 0.16. The result is found in the overdoped region and at high temperatures, therefore it cannot be explained with the pseudogap physics.

The Ram an scattering has been proposed as a complementary technique to ARPES to explore the kdependence of the quasiparticles due to its ability to select di erent regions of the Brillouin zone by changing the polarizations of incom ing and outgoing photons. In the point group D_{4h} of the square lattice, there are three di erent Ram an channels: B_{1g}, B_{2g} and A_{1g}. The B_{1g} channel projects out the antinodal region of the Ferm i surface, the B_{2g} the nodal region, and the A_{1g} is a weighted average over the entire Brillouin zone. The m entioned experiments refer to a strong anisotropy in the Ram an signal found from a com parison of the doping and tem perature dependence of the B_{1g} and B_{2g} signals.

The Ferm isurface of most hole-doped cuprates around optim al doping is close to a saddle point of the dispersion relation [5]. The possible relevance of this fact to the superconducting transition as well as to the anom alous behavior of the norm alstate was put forward in the early tim es of the cuprates and gave rise to the so-called Van Hove scenario [6]. A renorm alization group analysis at zero tem perature using the two-patch model[7] around the Van Hove points showed that the electron self-energy has the form of the one assumed in the marginal Fermi liquid [8]. As a consequence the quasiparticle spectral weight Z goes to zero logarithm ically at low energies. This result was reproduced using many-patch one-loop functional renorm alization group technique [9] where it is also shown that the scattering rate at high tem peratures is alm ost linear in frequency.

Renorm alization group calculations also show the pinning of the Ferm i level to the Van Hove singularity [10] what im plies that for lling fractions close and below the Van Hove lling, the low energy properties of the system will be dom inated by it. These features and the phase diagram make of the VH model a sensible microscopic model to address the low energy physics of the cuprates.

In reference [3] D evereaux establishes a relation between the B_{2g} signal with the in-plane optical conductivity and between the B_{1g} and the out of plane optical conductivity at low frequencies. It is shown that these similarities work quite well in B i 2212 and Y 123 but not in La 214. This last discrepancy is attributed to charge ordering e ects. However the general tendency shows that the in-plane m om entum is at least partially conserved in the c-axis transport. A round optim al lling the optical conductivity has an incoherent behavior what m atches with the result found in R am an for the B_{1g} signal (antinodal).

In ref. [4] a form alism was proposed to study the suppression of interlayer tunneling by inelastic processes in two dimensional systems in the clean limit. A relation was established between departure from Ferm i liquid behavior driven by electron correlations inside the layers and the out of plane coherence. There it was shown that the out of plane hopping is always irrelevant if the Ferm i level of the interacting electrons lies at a Van Hove singularity.

The renormalization group approach is a technique well suited for weak coupling, therefore it might be appropriate to study the optim al-overdoped region where the e ective interaction is weaker. W e propose as a possible explanation of the metal-insulator transition found in the B_{1q} signal (antinodal) the incoherence of the transport when the chem ical potential of the planes is close to the Van Hove lling. For lling fractions close and below the singularity, the Van Hove lling is an attractive point in the renorm alization group sense and the transport should be incoherent up to the Van Hove lling. Above the Van Hove lling the ow of the chem ical potential drives the system away of the singularity area and the system recovers a Ferm i liquid behavior. W ithin this scenario we can also understand the incoherent behavior of the c-axis optical conductivity in two di erent ways: either through

the relation between the R am an signal B_{1g} and the c-axis optical conductivity at low frequencies [3], or through the prediction of incoherent transport when the chem ical potential is at or below the Van H ove lling [4].

In reference [1] a phenom enologicalm odelw as proposed to explain the metal insulator transition in the antinodal region by invoking the opening of an anisotropic gap in the hot spots region (Van Hove region). This gap can be seen as the threshold energy where these e ects take place. In the Van Hove scenario nodal quasiparticles are naturally di erent from antinodal, the form er being strongly renorm alized by scattering between the VH points. Our proposal then is compatible with the opening of an anisotropic gap, in fact it provides a physical origin for the gap. In addition the Van Hove quasiparticles have a lifetime compatible with the marginal Ferm i liquid. It also agrees with the recent proposal put forward in [12] to explain the intraplane optical conductivity and the caxis optical conductivity based on the di erence between nodal and antinodal quasiparticles.

To illustrate these ideas we make a simple calculation. We compute the R am an response in the absence of vertex corrections [2]:

$${}^{(0)}(q = 0;) = \frac{2}{N} \sum_{k}^{X} {}^{2}(k) \sum_{k}^{Z} \frac{d!}{d!} [f(!) f(! +)]$$

$$G^{(0)}(k; !) G^{(0)}(k; ! +)$$
(1)

where f(!) is the Ferm i factor, $G^{(0)}(k; !)$ is the imaginary part of the G reen function of the electron, (k) is the Raman vertex corresponding to di erent channels = B_{1g} ; B_{2g} and the sum is all over the B rillouin zone. The expressions for the unrenormalized Raman vertices are $B_{1g}(k) = a(\cos k_x - \cos k_y)$ and $B_{2g}(k) = b(\sin k_x \sin k_y)[2]$ where we have absorbed constant factors in the a and b parameters.

The electron self-energy in the Van Hove model has the form [7]:

$$_{\rm V\,H}$$
 (!) = 2 ! $\log \frac{!}{!_{\rm c}}$ i j! j; (2)

where is a dimensionless coupling constant which is proportional to the onsite interaction, $/(U=t)^2$, and $!_c$ is a cuto . We assume that this self-energy is a good approximation at high temperature based on calculations using functional renormalization group [9].

This self-energy is inserted in the spectral function A(k;!) = 2 Im G(k;! + i) where:

$$A (k;!) = \frac{\text{Im } (k;!)}{(! + k \text{ Re } (k;!))^2 + \text{Im } (k;!)^2};$$
(3)

where (k;!) is the self-energy due to either in purities or coupling to inelastic scattering coming from Van Hove physics and $_{k} = 2t(\cos k_{x} + \cos k_{y}) - 4t^{0}\cos k_{x}\cos k_{y}$. The A (k;!) is inserted in the Ram an scattering given by Eq. (1). The results for the B_{1g} signal in units of t are

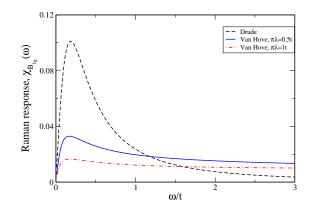


FIG.1: R am an signal for B_{1g} channels for the conventional D rude behavior and for a system close to the V an H ove lling. The calculations have been done for $t^0 = 0.3t$ and T = 300K for di erent coupling constants.

shown in Fig.1 where the standard D rude case (dashed curve) with a constant scattering rate of Im = 0.1tis shown for comparison. To the imaginary part of the self energy in the Van Hove model we have also added a constant scattering rate turning up to be: Im = j! j. W e can identify the peak at a frequency of 0:1+ twice the scattering rate ! = 0.2t in the D rude curve. For the Van Hove case we observe that the peak is already strongly reduced for a coupling constant of = 0:5t, and can be completely washed out for bigger coupling constant, = 1t, showing the incoherent behavior. In our argum ent the three curves in Fig.1 would correspond to llings where the chem ical potential is pinned at Van Hove lling (Van Hove curve for = 1t), llings closer to Van Hove lling (Van Hove curve for = 0:5t, and llings above the Van Hove lling (D rude curve). W e think that higher values of the coupling constant correspond to decreasing dopings in cuprates being closer to the M ott insulator.

In order to describe more quantitatively the metalinsulator transition a full calculation must be performed varying the doping around the Van Hove lling[11]. We however believe that the simple argument provided in this paper may illustrate the physics of the problem.

W ithin our scheme we can also address the tem perature dependence of the Ram an signal found in [1]. The signal B_{2q} corresponding to the nodal quasiparticles is relatively doping independent and decreases with increasing temperature showing a conventional behavior. In contrast, the signalB_{1q} corresponding to antinodal quasiparticles varies strongly with doping showing di erent tem perature dependence for di erent regions of dopings. In the strongly overdoped region (p 0:22) both B_{1g} and B_{2g} R am an signals decrease with increasing tem perature, a sign of metallic behavior. For dopings in the range 0:16 р 0:20 the B_{1q} signal becomes essentially tem perature independent, and nally, below optim aldoping it increases with tem perature. W e can understand this behavior qualitatively as due to the proxim ity of the chemical potential to the Van H ove singularity. Below and close to Van H ove lling the quasiparticles can be therm ally excited, showing a semiconductor behavior. In the strongly overdoped region we are far from the inuence of Van H ove and the behavior is the one expected in a conventional metal. We do not have a clear understanding of the intermediate region 0.16 p 0.22. In reference [1] it is argued that p = 0.22 corresponds to a quantum critical point where the anisotropy between the B_{1g} and B_{2g} signals disappears. This feature goes beyond the scope of the present study.

In all these qualitative arguments one should bear in mind that the behavior seen in experiments is attached to the fully interacting system and not to the free one. Therefore we cannot determ ine where is the Van Hove lling of the free theory. Although in ARPES experim ents [5] they can observe an extended singularity, the spectral function A $(k_{fixed}; !)$ is extremely broad and cannot be thought of as quasiparticles. That m eans that any singularity in the density of states is washed out. This result is consistent with other experiments such as tunneling and optical measurements where no singularity in the density of states is observed. This does not m ean that the Van H ove singularity is not relevant for the physics we are interested in, on the contrary, it is near the singularity where one can expect a rich physics driven by the interactions of the enhanced density of states which

encodes competing instabilities and deform ation of the Ferm i surface[6, 14]. The situation is similar to the one related with the presence of a quantum critical point that can be inferred by nearby anomalies at nite temperatures. In fact the Van Hove point is a quantum critical point as the divergence of the density of states and the various response functions at the critical doping occurs at zero temperature. We believe that the region of in uence of the Van Hove singularity is somewhere between optim al and overdoped doping because this is the region where a dip in the Hall number is seen [13] and where the renorm alized Ferm i surface seen by ARPES shows an extended singularity [5].

In sum m ary, we propose that the m etal-insulator transition observed in R am an scattering in the antinodal region of B ISCO is driven by the incoherence of the transport set by the strong scattering su ered by antinodal quasiparticles when the chem ical potential is below or at the V an H ove singularity.

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